

High-Current Complementary Silicon Transistors

... for use as output devices in complementary general purpose amplifier applications.

- High DC Current Gain —
 $h_{FE} = 1000 \text{ (Min) @ } I_C = 20 \text{ A dc}$
- Monolithic Construction with Built-in Base Emitter Shunt Resistor
- Junction Temperature to +200°C

MAXIMUM RATINGS

Rating	Symbol	MJ11012	MJ11015 MJ11016	Unit
Collector-Emitter Voltage	V_{CEO}	60	120	Vdc
Collector-Base Voltage	V_{CB}	60	120	Vdc
Emitter-Base Voltage	V_{EB}	5		Vdc
Collector Current	I_C	30		A dc
Base Current	I_B	1		A dc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C @ $T_C = 100^\circ\text{C}$	P_D	200 1.15		Watts W/°C
Operating Storage Junction Temperature Range	T_J, T_{stg}	-55 to +200		°C

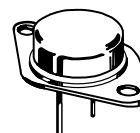
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.87	°C/W
Maximum Lead Temperature for Soldering Purposes for ≤ 10 Seconds.	T_L	275	°C

PNP
MJ11015
NPN
MJ11012
MJ11016*

*ON Semiconductor Preferred Device

**30 AMPERE
 DARLINGTON
 POWER TRANSISTORS
 COMPLEMENTARY
 SILICON
 60-120 VOLTS
 200 WATTS**



**CASE 1-07
 TO-204AA
 (TO-3)**

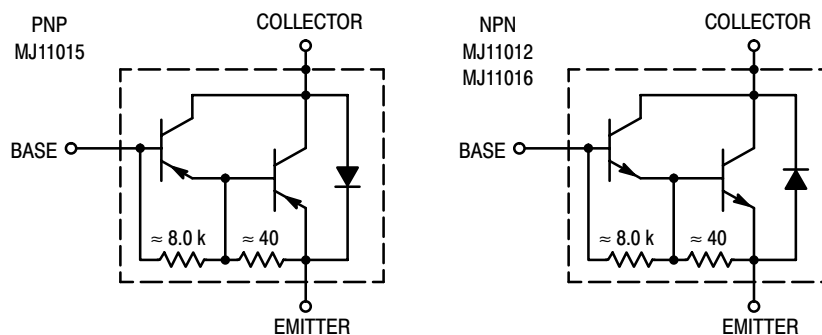


Figure 1. Darlington Circuit Schematic

Preferred devices are ON Semiconductor recommended choices for future use and best overall value.

MJ11015 MJ11012 MJ11016

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted.)

Characteristics	Symbol	Min	Max	Unit
-----------------	--------	-----	-----	------

OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage(1) ($I_C = 100\text{ mA}$, $I_B = 0$)	MJ11012 MJ11015, MJ11016	$V_{(BR)CEO}$	60 120	— —	Vdc
Collector–Emitter Leakage Current ($V_{CE} = 60\text{ Vdc}$, $R_{BE} = 1\text{ k ohm}$)	MJ11012	I_{CER}	—	1	mAdc
($V_{CE} = 120\text{ Vdc}$, $R_{BE} = 1\text{ k ohm}$)	MJ11015, MJ11016		—	1	
($V_{CE} = 60\text{ Vdc}$, $R_{BE} = 1\text{ k ohm}$, $T_C = 150^\circ\text{C}$)	MJ11012		—	5	
($V_{CE} = 120\text{ Vdc}$, $R_{BE} = 1\text{ k ohm}$, $T_C = 150^\circ\text{C}$)	MJ11015, MJ11016		—	5	
Emitter Cutoff Current ($V_{BE} = 5\text{ Vdc}$, $I_C = 0$)		I_{EBO}	—	5	mAdc
Collector–Emitter Leakage Current ($V_{CE} = 50\text{ Vdc}$, $I_B = 0$)		I_{CEO}	—	1	mAdc

ON CHARACTERISTICS(1)

DC Current Gain ($I_C = 20\text{ Adc}$, $V_{CE} = 5\text{ Vdc}$) ($I_C = 30\text{ Adc}$, $V_{CE} = 5\text{ Vdc}$)	h_{FE}	1000 200	— —	—
Collector–Emitter Saturation Voltage ($I_C = 20\text{ Adc}$, $I_B = 200\text{ mAdc}$) ($I_C = 30\text{ Adc}$, $I_B = 300\text{ mAdc}$)	$V_{CE(sat)}$	— —	3 4	Vdc
Base–Emitter Saturation Voltage ($I_C = 20\text{ A}$, $I_B = 200\text{ mAdc}$) ($I_C = 30\text{ A}$, $I_B = 300\text{ mAdc}$)	$V_{BE(sat)}$	— —	3.5 5	Vdc

DYNAMIC CHARACTERISTICS

Current–Gain Bandwidth Product ($I_C = 10\text{ A}$, $V_{CE} = 3\text{ Vdc}$, $f = 1\text{ MHz}$)	h_{fe}	4	—	MHz
--	----------	---	---	-----

(1) Pulse Test: Pulse Width = $300\text{ }\mu\text{s}$, Duty Cycle $\leq 2.0\%$.

MJ11015 MJ11012 MJ11016

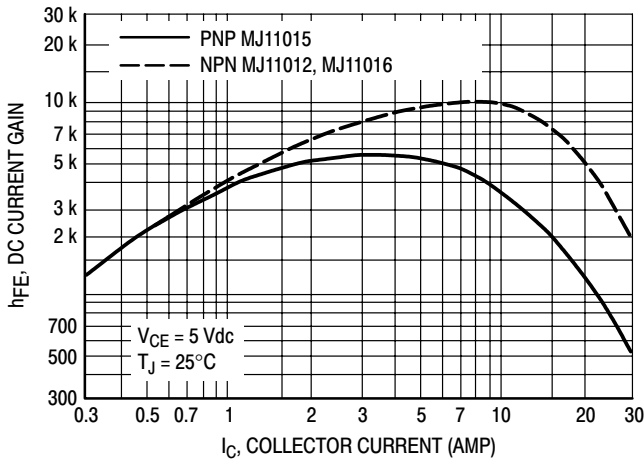


Figure 2. DC Current Gain (1)

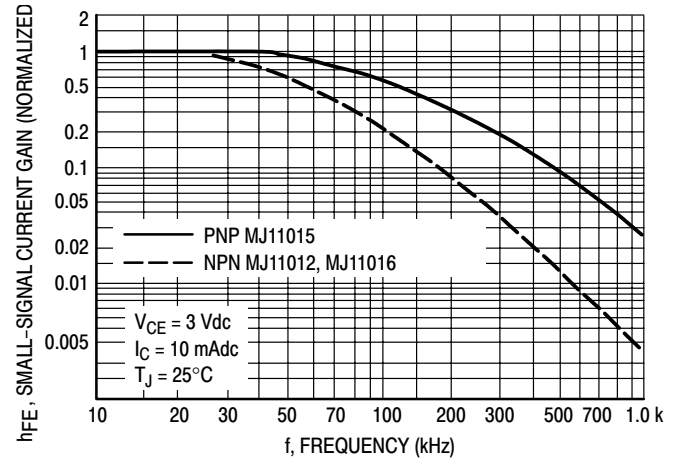


Figure 3. Small-Signal Current Gain

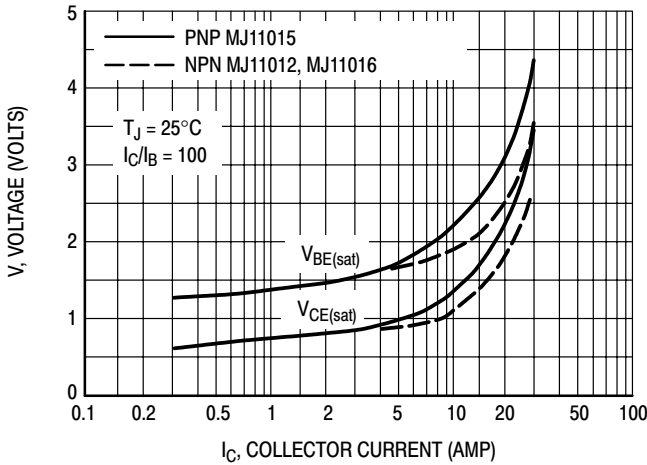


Figure 4. "On" Voltages (1)

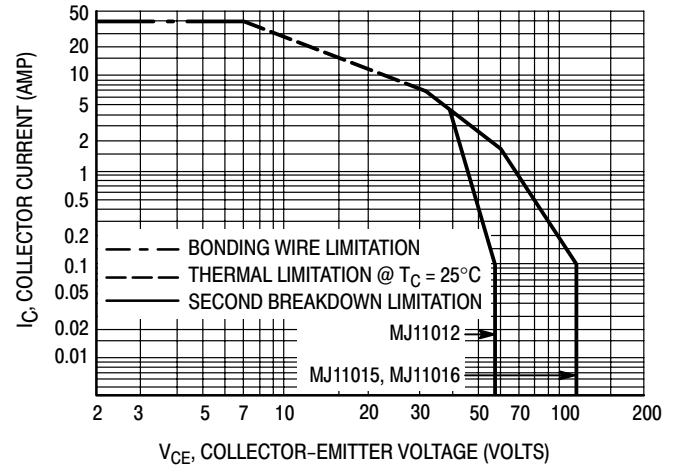
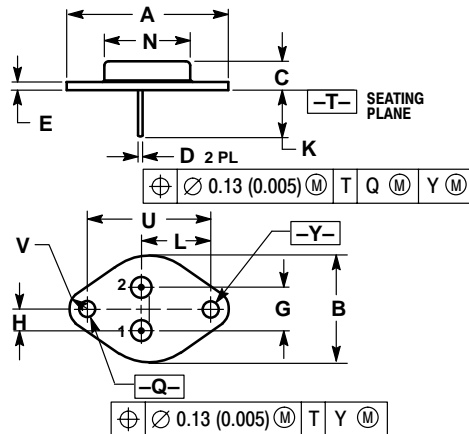


Figure 5. Active Region DC Safe Operating Area

There are two limitations on the power handling ability of a transistor average junction temperature and secondary breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operations e.g., the transistor must not be subjected to greater dissipation than the curves indicate.

At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by secondary breakdown.

PACKAGE DIMENSIONS

CASE 1-07
TO-204AA (TO-3)
ISSUE Z

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. ALL RULES AND NOTES ASSOCIATED WITH REFERENCED TO-204AA OUTLINE SHALL APPLY.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.550 REF		39.37 REF	
B	---	1.050	---	26.67
C	0.250	0.335	6.35	8.51
D	0.038	0.043	0.97	1.09
E	0.055	0.070	1.40	1.77
G	0.430 BSC		10.92 BSC	
H	0.215 BSC		5.46 BSC	
K	0.440	0.480	11.18	12.19
L	0.665 BSC		16.89 BSC	
N	---	0.830	---	21.08
Q	0.151	0.165	3.84	4.19
U	1.187 BSC		30.15 BSC	
V	0.131	0.188	3.33	4.77

STYLE 1:

1. BASE
 2. EMITTER
- CASE: COLLECTOR

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer.

PUBLICATION ORDERING INFORMATION

NORTH AMERICA Literature Fulfillment:

Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: ONlit@hibbertco.com
Fax Response Line: 303-675-2167 or 800-344-3810 Toll Free USA/Canada

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

EUROPE: LDC for ON Semiconductor – European Support

German Phone: (+1) 303-308-7140 (Mon-Fri 2:30pm to 7:00pm CET)
Email: ONlit-german@hibbertco.com
French Phone: (+1) 303-308-7141 (Mon-Fri 2:00pm to 7:00pm CET)
Email: ONlit-french@hibbertco.com
English Phone: (+1) 303-308-7142 (Mon-Fri 12:00pm to 5:00pm GMT)
Email: ONlit@hibbertco.com

EUROPEAN TOLL-FREE ACCESS*: 00-800-4422-3781

*Available from Germany, France, Italy, UK, Ireland

CENTRAL/SOUTH AMERICA:

Spanish Phone: 303-308-7143 (Mon-Fri 8:00am to 5:00pm MST)
Email: ONlit-spanish@hibbertco.com
Toll-Free from Mexico: Dial 01-800-288-2872 for Access –
then Dial 866-297-9322

ASIA/PACIFIC: LDC for ON Semiconductor – Asia Support

Phone: 1-303-675-2121 (Tue-Fri 9:00am to 1:00pm, Hong Kong Time)
Toll Free from Hong Kong & Singapore:
001-800-4422-3781
Email: ONlit-asia@hibbertco.com

JAPAN: ON Semiconductor, Japan Customer Focus Center

4-32-1 Nishi-Gotanda, Shinagawa-ku, Tokyo, Japan 141-0031
Phone: 81-3-5740-2700
Email: r14525@onsemi.com

ON Semiconductor Website: <http://onsemi.com>

For additional information, please contact your local Sales Representative.